

Serial No. 10/673,484

Docket No.: 300.1132

IN THE CLAIMS:

The text of all pending claims, (including withdrawn claims) is set forth below. Cancelled and not entered claims are indicated with claim number and status only. The claims as listed below show added text with underlining and deleted text with ~~striketrough~~. The status of each claim is indicated with one of (original), (currently amended), (cancelled), (withdrawn), (new), (previously presented), or (not entered).

Please AMEND claims 1, 3, 4, and 5 in accordance with the following:

1. (CURRENTLY AMENDED) A thin-film capacitor device, comprising:
a lower electrode formed on a surface of a core substrate;
a metal film region and a dielectric film region which are formed by selective anodic oxidation into generated from a metal film formed on said lower electrode;
an upper electrode formed on said dielectric film region; and
a first conductor extending from said lower electrode toward an opposite surface of said core substrate, ~~wherein;~~
a first electrode pad is provided on said first conductor;
and a second electrode pad is provided on a second conductor connected to said upper electrode; and
a third conductor provided on said metal film region.

2. (CANCELED)

3. (CURRENTLY AMENDED) A thin-film capacitor device as claimed in claim 2, wherein said metal film is made of tantalum or titanium, ~~and~~
~~said dielectric film is generated by anodic oxidation of said tantalum or titanium.~~

4. (CURRENTLY AMENDED) A thin-film capacitor device, comprising:
~~as claimed in claim 2, wherein~~ a lower electrode formed on a first surface of a core
substrate;
a dielectric film made from a metal film formed on said lower electrode;
an upper electrode formed on said dielectric film; and
a first conductor extending from said lower electrode toward an opposite, second
surface of said core substrate, wherein;
a first electrode pad is provided on said first conductor and a second electrode pad is
connected to said upper electrode, wherein by selective anodic oxidation, said metal film is divided into a dielectric film region and a first and a second metal film region,

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said first conductor connected to said lower electrode is connected to a lower surface of said first metal film region,

a third conductor is connected to an upper surface of said first metal film region,

said second conductor connected to said upper electrode is connected to an upper surface of said second metal film region, and

a fourth conductor is connected to a lower surface of said second metal film region, and wherein

first to fourth electrode pads are provided on said first to fourth conductors, respectively, and a capacitor is formed by said dielectric film region, said upper electrode, and said lower electrode.

5. (CURRENTLY AMENDED) A thin-film capacitor device as claimed in claim 4, wherein said metal film is made of tantalum or titanium, and
~~said dielectric film is generated by anodic oxidation of said tantalum or titanium.~~

6. (ORIGINAL) A thin-film capacitor device mounting module containing a thin-film capacitor device and a multilayer wiring circuit having external connection terminals, wherein said thin-film capacitor device comprises:

a dielectric film region and a first and a second metal film region into which a metal film formed on a core substrate is divided by selective anodic oxidation;

a first conductor connected to a lower electrode at a lower surface of said first metal film region;

a third conductor connected to an upper surface of said first metal film region;

a second conductor connected to an upper electrode at an upper surface of said second metal film region; and

a fourth conductor connected to a lower surface of said second metal film region, and wherein:

first to fourth electrode pads are provided on said first to fourth conductors, respectively, and a capacitor is formed by said dielectric film region, said upper electrode, and said lower electrode, and

said first electrode pad and said fourth electrode pad provided on said thin-film capacitor device are connected to said multilayer wiring circuit, and a semiconductor device is connected to said second electrode pad and said third electrode pad provided on said thin-film capacitor device.

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7. (ORIGINAL) A thin-film capacitor device mounting module as claimed in claim 6, wherein
- said module contains a plurality of said thin-film capacitor devices, and
 - said first electrode pad and said fourth electrode pad provided on each of said thin-film capacitor devices are connected to said multilayer wiring circuit.